



Agent's Docket No. 12591-US

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of )  
Siegfried JANZ et al )  
Serial No: <sup>10</sup>29/054,911 ) Art Unit: 2874  
Filed: 25-January-2002 ) Examiner:

**For: METHOD FOR POLARIZATION BIREFRINGENCE COMPENSATION IN A  
WAVEGUIDE DEMULTIPLEXER USING A COMPENSATOR WITH A HIGH  
REFRACTIVE INDEX CAPPING LAYER**

April 5, 2002

Commissioner of Patent and Trademarks  
Washington, D.C. 20231

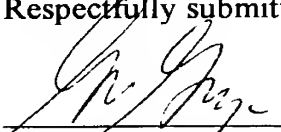
**TRANSMITTAL LETTER**

Sir:

Please find enclosed for filing:

- Response to Notice of Omitted Items dated February 11, 2002
- Marked up Version to Show Changes Made

Respectfully submitted,

  
George M. MacGregor  
Registration No. 37,547  
Agent of Record

MARKS & CLERK  
P. O. Box 957, Station B,  
Ottawa, Ontario Canada K1P 5S7 (613) 236-9561

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**RESPONSE TO NOTICE OF OMITTED ITEM(S) DATED FEBRUARY 11, 2002**

Sir:

In response to the Notice of Omitted Items dated February 11, 2002, applicants respectfully request that the application be amended as follows by way of Preliminary Amendment:

**In the Specification:**

Please cancel the paragraph on page 5, at line 14 and 15.

Please replace the paragraph on page 11, beginning at line 9 with the following rewritten paragraph:

- - In a further embodiment, a lower refractive index overlying layer of  $\text{SiO}_2$  ( $N \cong 1.46$ ) is deposited on top of the silicon nitride layer 15 ( $N \cong 1.9$ ). The strength of the compensator is adjusted by varying the thickness of this overlying  $\text{SiO}_2$  layer. The change in  $\Delta\lambda$  with oxide thickness is now approximately three times smaller than for an identical change in the thickness of the nitride layer 15. - -